(Tc = 25°C unless otherwise specified)

$V_{DS,max}$	Drain source voltage	1200	V	V_{GS} = 0V, I_D = 100μA	
$V_{GS,max}$	Gate source voltage	-8 /+22	V	Absolute maximum values	Note1
$V_{GSpulse}$	Gate-source voltage,max. transient voltage	-10 /+25	V	$t_p \leq 0.5\mu s$, D 0.01	
V_{GSop}	Gate source voltage	-4 /+15~18	V	Recommended operational values	
I_D	Cn?de				

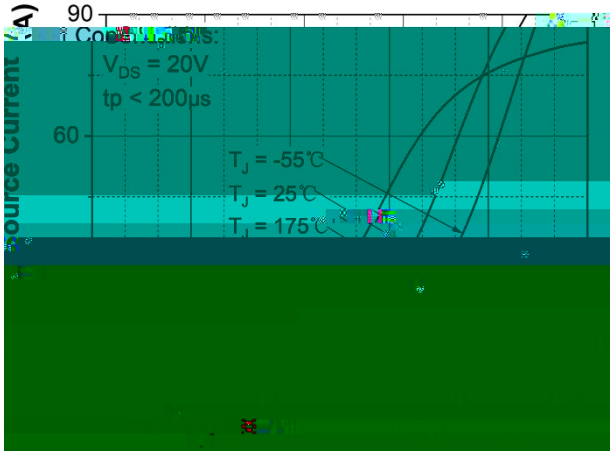


Figure 7. Transfer characteristic for various junction temperatures

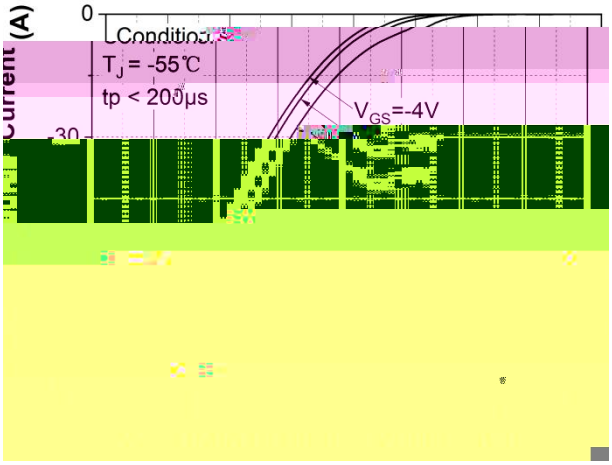


Figure 8. Body diode characteristic at T_J = -55 ºC

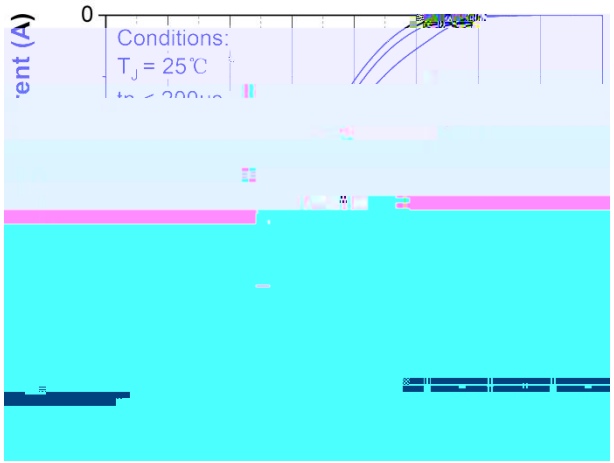


Figure 9. Body diode characteristic at T_J = 25 ºC

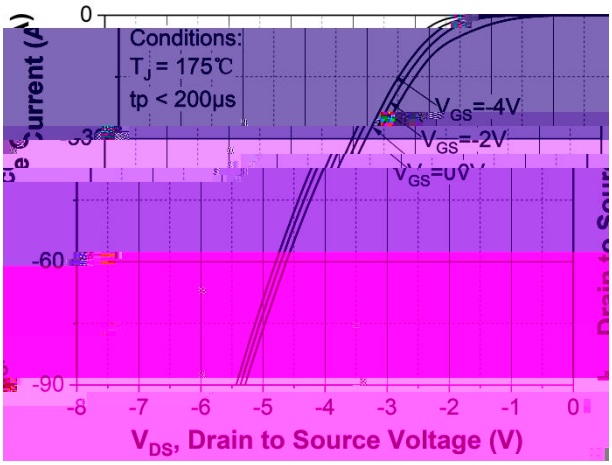


Figure 10. Body diode characteristic at T_J = 175ºC

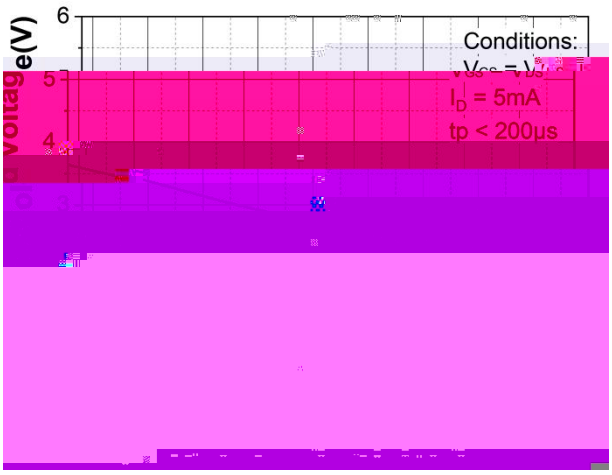


Figure 11. Threshold voltage vs. temperature

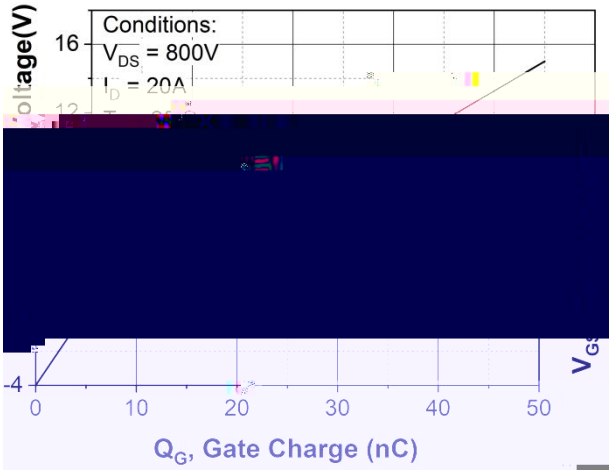


Figure 12. Gate charge characteristic

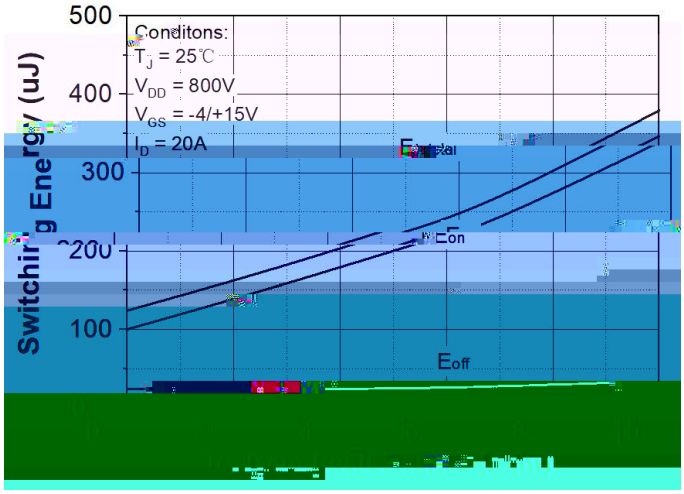


Figure 25. Clamped inductive switching energy vs. R_G(ext)

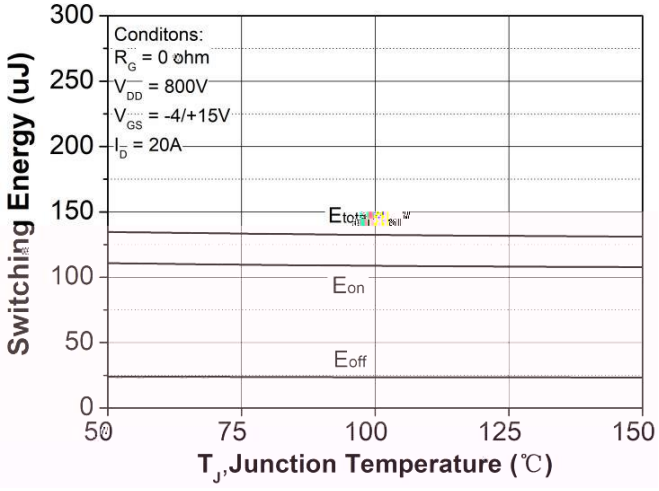


Figure 26. Reverse characteristics vs.T_J

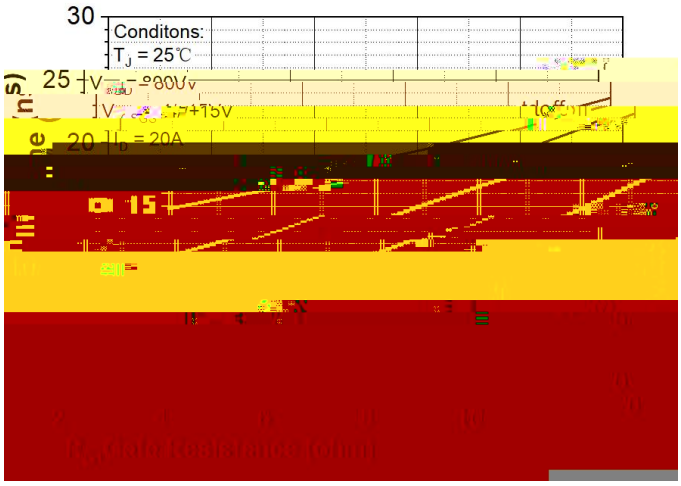


Figure 27. Switching times vs. R_G (ext)

(TO-263-7L-A)

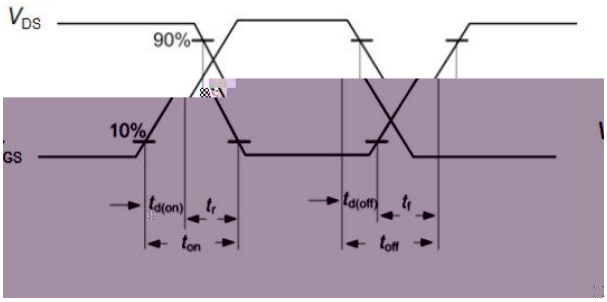


Figure A. Definition of switching times

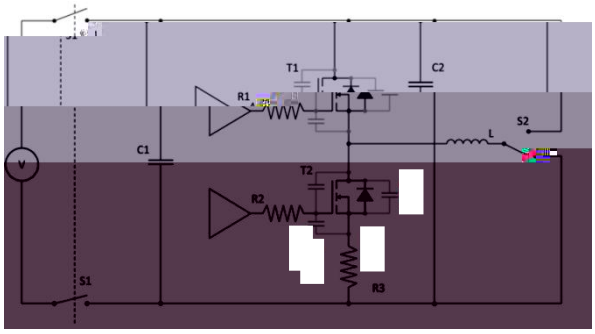


Figure B. Dynamic test circuit

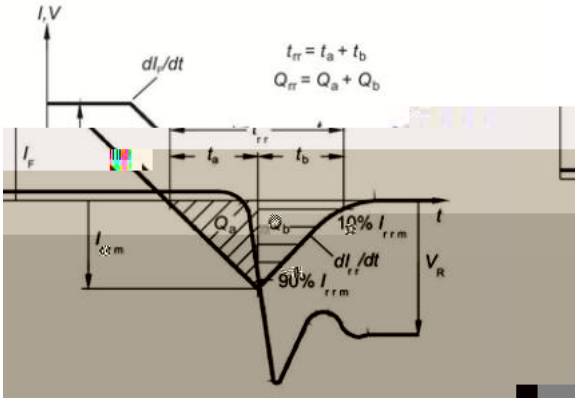


Figure C. Definition of body diode switching characteristics

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		——	——
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1.
The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/ EC (RoHS2), as implemented January 2, 2013.

2.
REACh

6. Due to technical requirements products may contain dangerous substances.